

0057-2533-2YY CONT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

HIDEKI TAKAHASHI

SERIAL NO.: 09/421,217

RCE FILED: February 7, 2002

FOR: INSULATED GATE SEMICONDUCTOR
DEVICE WITH LOW ON VOLTAGE
AND MANUFACTURING METHOD
THEREOF (AS AMENDED)

: GROUP ART UNIT: 2811

: EXAMINER: LOKE, S.

2/11/03

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3/12/03

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AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action of November 6, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend Claim 22 to read as follows:¹

figs. 3, 22, 23

F1

22. (Four Times Amended) An insulated gate semiconductor device, comprising:
a first semiconductor layer of a first conductivity type having first and second main
surfaces on opposite sides thereof;
a second semiconductor layer of a second conductivity type provided on said first
main surface of said first semiconductor layer;

¹A marked-up copy of the amendments is attached hereto.